

## NCE N-Channel Enhancement Mode Power MOSFET

#### **Description**

The NCE0110AK uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

#### **General Features**

V<sub>DS</sub> =100V,I<sub>D</sub> =10A

 $R_{DS(ON)}$  < 110m $\Omega$  @  $V_{GS}$ =10V

 $R_{DS(ON)} < 120 m\Omega$  @  $V_{GS} = 4.5 V$ 

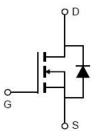
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E<sub>AS</sub>
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

#### **Application**

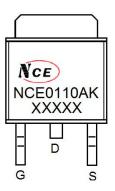
- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

100% UIS TESTED!

100% ΔVds TESTED!



Schematic diagram



Marking and pin assignment



TO-252-2L top view

#### **Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE0110AK	NCE0110 AK	TO-252-2L	-	-	-

## Absolute Maximum Ratings (T<sub>C</sub>=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	100	V
Gate-Source Voltage	V <sub>G</sub> s	±20	V
Drain Current-Continuous	I <sub>D</sub>	10	А
Drain Current-Continuous(T <sub>C</sub> =100 °C)	I <sub>D</sub> (100°C)	7	А
Pulsed Drain Current	I <sub>DM</sub>	40	А
Maximum Power Dissipation	P <sub>D</sub>	40	W
Derating factor		0.27	W/℃
Single pulse avalanche energy (Note 5)	Eas	20	mJ
Operating Junction and Storage Temperature Range	$T_{J}, T_{STG}$	-55 To 175	°C



#### **Thermal Characteristic**

Thermal Resistance,Junction-to-Case <sup>(Note 2)</sup>	Rejc	3.8	°C/W
Maximum Junction-to-Ambient	R <sub>θJA</sub>	60	°C/W

## Electrical Characteristics (T<sub>C</sub>=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics				•		
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250µA	100	110	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =100V,V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS},I_{D}=250\mu A$	1.0	1.5	2.0	V
Dunin Course On Chata Desintance	Б	V <sub>GS</sub> =10V, I <sub>D</sub> =10A	-	-	110	mΩ
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =8A	-	-	120	
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =25V,I <sub>D</sub> =6A	3.5	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	Clss	\/ 50\/\/ 0\/	-	714	-	PF
Output Capacitance	Coss	V <sub>DS</sub> =50V,V <sub>GS</sub> =0V, - 32		-	PF	
Reverse Transfer Capacitance	Crss	F=1.0MHz	-	27	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>		-	11	-	nS
Turn-on Rise Time	t <sub>r</sub>	$V_{DD}$ =50V, $R_L$ =15 $\Omega$	-	7.4	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =10 $V$ , $R_{G}$ =2.5 $\Omega$	-	35	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	9.1	-	nS
Total Gate Charge	Qg	V 50VI 40A	-	21.8		nC
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS}$ =50V, $I_{D}$ =10A, $V_{GS}$ =10V	-	2.7	-	nC
Gate-Drain Charge	$Q_{gd}$	VGS-10V	-	5	-	nC
Drain-Source Diode Characteristics			•			
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =10A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	10	Α
Reverse Recovery Time	t <sub>rr</sub>	TJ = 25°C, IF =10A	-	21		nS
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note3)}$	-	97		nC
Forward Turn-On Time	ton	Intrinsic turn-on time is negl	igible (tur	n-on is do	ominated b	y LS+LD

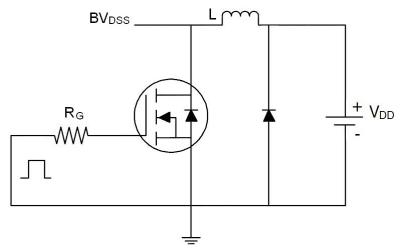
#### Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board,  $t\,\leqslant\,$  10 sec.
- 3. Pulse Test: Pulse Width  $\, \leqslant \, 300 \, \mu \, \text{s}$ , Duty Cycle  $\, \leqslant \, 2\%$ .
- 4. Guaranteed by design, not subject to production
- **5.** E<sub>AS</sub> condition: Tj=25  $^{\circ}\text{C}$  ,V<sub>DD</sub>=50V,V<sub>G</sub>=10V,L=0.5mH,Rg=25 $\Omega$

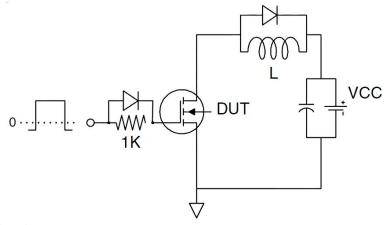


## **Test Circuit**

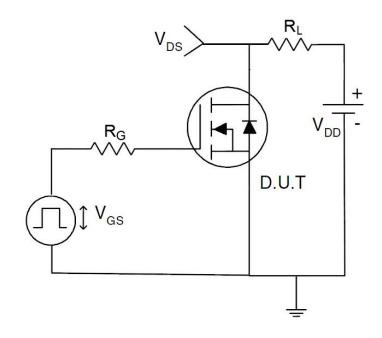
# 1) E<sub>AS</sub> test Circuit



## 2) Gate charge test Circuit

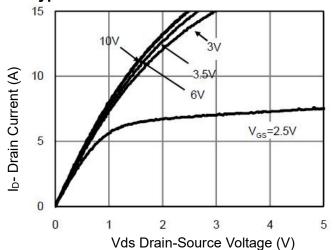


## 3) Switch Time Test Circuit

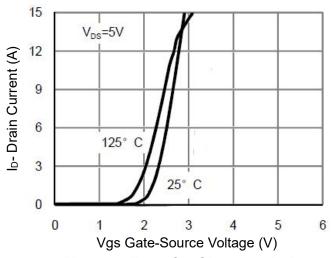




## Typical Electrical and Thermal Characteristics (Curves)



**Figure 1 Output Characteristics** 



**Figure 2 Transfer Characteristics** 

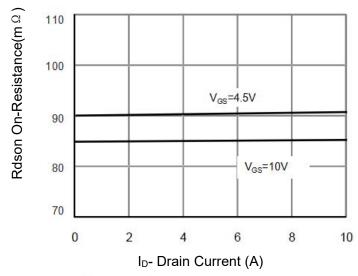


Figure 3 Rdson- Drain Current

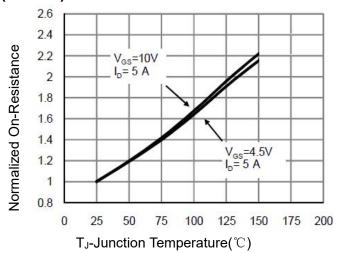


Figure 4 Rdson-JunctionTemperature

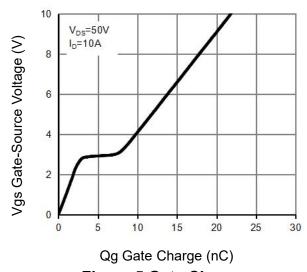


Figure 5 Gate Charge

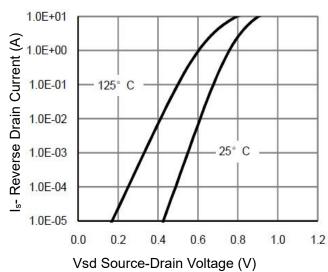
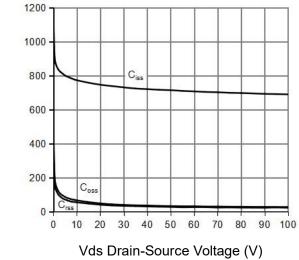
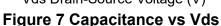


Figure 6 Source- Drain Diode Forward



C Capacitance (pF)





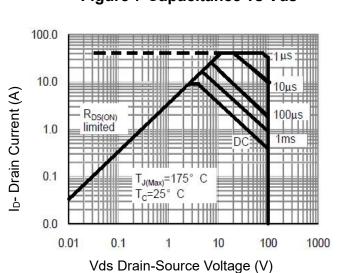


Figure 8 Safe Operation Area

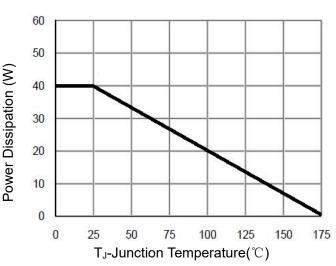


Figure 9 Power De-rating

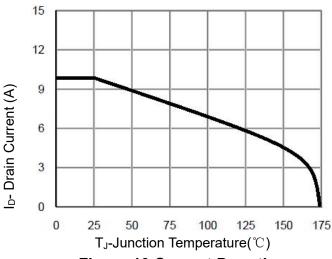
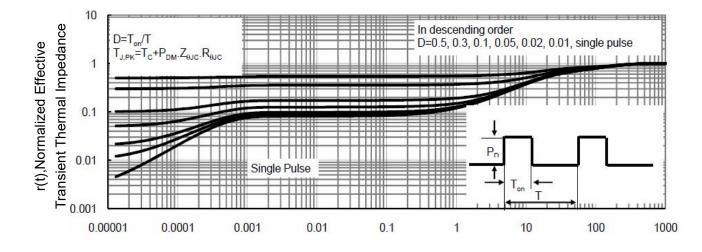


Figure 10 Current De-rating

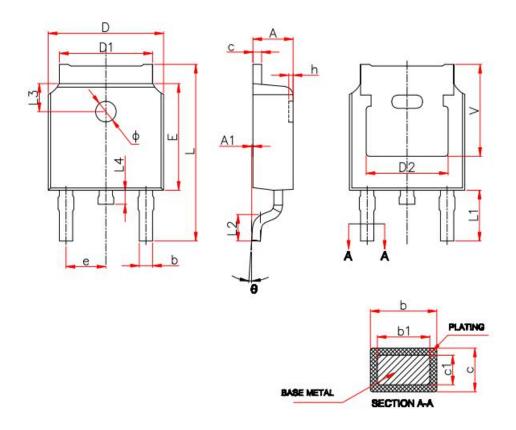


Square Wave Pluse Duration(sec)

**Figure 11 Normalized Maximum Transient Thermal Impedance** 



# **TO-252 Package Information**



Cumbal	Millimeters		
Symbol -	Min.	Max.	
Α	2.20	2.40	
A1	0.00	0.13	
b	0.66	0.86	
b1	0.73	0.79	
С	0.46	0.58	
c1	0.50	0.52	
D	6.50	6.70	
D1	5.10	5.46	
D2	4.83 REF.		
Е	6.00	6.20	
е	2.19	2.39	
L	9.80	10.40	
L1	2.90 REF.		
L2	1.40	1.70	
L3	1.60 REF.		
L4	0.60	1.00	
Φ	1.10	1.30	
θ	0°	8°	

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